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**Growth-induced electronic properties of epitaxial graphene<sup>1</sup>**

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The growth of epitaxial graphene on silicon carbide is challenging to understand and control, yet rife with scientific and technological opportunities. This is due in part to different growth-induced structures such as the “moire” alignment of graphene layers in multilayer epitaxial graphene on SiC(000 $\bar{1}$ ) and the formation of sidewall ribbons at natural and lithographically-defined SiC(0001) step-bunches (nanofacets). We apply scanning tunneling microscopy (STM) and spectroscopy (STS) to probe the local energy bands of such growth-induced structures. STS at cryogenic temperatures and large magnetic fields creates a comb of discrete Landau level energies that we use to quantitatively characterize the local electronic properties.

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